	Application No.	Applicant(s)
Notice of Allowability	10/684,424	ISHII ET AL.
	Examiner	Art Unit
	Andy Huynh	2818
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this or other appropriate communica GHTS. This application is subje-	application. If not included tion will be mailed in due course. THIS
1. 🔀 This communication is responsive to the Amendment dated	<u>d 07/25/2005</u> .	• •
2. The allowed claim(s) is/are 1-5 and 8.		
3. X The drawings filed on 25 July 2005 are accepted by the Ex	aminer.	
 4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). 	been received. been received in Application No	· -
* Certified copies not received:	•	
Applicant has THREE MONTHS FROM THE "MAILING DATE" on noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		ply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give		
6. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.	
(a) ☐ including changes required by the Notice of Draftspers	on's Patent Drawing Review (P	ΓΟ-948) attached
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		
 (b) ☐ including changes required by the attached Examiner's Paper No./Mail Date 	s Amendment / Comment or in th	e Office action of
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the		
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I		
Attachment(s)		
1. Notice of References Cited (PTO-892)	5. Notice of Information	al Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summ	ary (PTO-413), Data
3. 🛛 Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 10/15/2003	Paper No./Mail 8), 7. ⊠ Examiner's Ame	ndment/Comment
4. Examiner's Comment Regarding Requirement for Deposit	-	ement of Reasons for Allowance
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DETAILED ACTION

In the Amendment dated July 25, 2005, the specification, Figs. 2, 10, 13 and Claims 1-5 and 8 are amended.

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

This application is in condition for allowance except for the presence of nonelected claims 6, 7 and 9-15 without traverse. Accordingly, claims 6, 7 and 9-15 have been canceled.

Allowable Subject Matter

Claims 1-5 and 8 are allowed.

The following is an examiner's statement of reason for allowance:

Claim 1 is allowable over the prior art of record because the prior art of record does not teach or render obvious a semiconductor memory device comprises an inversion layer region to be formed on the surface upon application of a voltage to the first electrode, the charge storage region being controlled by the second electrode such that information is stored by use of a characteristic that conductance between the diffusion layer and the inversion layer region

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changes according to an amount of charge stored in the charge storage region, and in combination with all other features as recited in independent claim 1.

Claim 2-5 and 8 is allowable over the prior art of record because the prior art of record does not teach or render obvious a semiconductor memory device comprises an inversion layer region to be formed on the surface upon application of a voltage to the first electrode, and a third diffusion layer of the second conduction type which is formed such that it overlaps with one end of the inversion layer region, the potential of said first charge storage region and said second charge storage region being controlled by said second electrode such that information is stored by use of a characteristic that conductance between said first diffusion layer and said third diffusion layer changes according to an amount of charge stored in said first charge storage region and information is stored by use of a characteristic that conductance between said second diffusion layer and said third diffusion layer changes according to an amount of charge stored in said second charge storage region, and in combination with all other features as recited in independent claim 2.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Andy Huynh whose telephone number is (571) 272-1781. The examiner can normally be reached on Monday-Friday 8:30am-5:00pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (571) 273-8300 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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Andy Huynh

God Muyo

08/08/05

Patent Examiner